

Choong Hee Lee

List of Publications by Year in descending order

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13
papers

1,172
citations

1051969

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1427216

11
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13
all docs

13
docs citations

13
times ranked

3053
citing authors

#	ARTICLE	IF	CITATIONS
1	Molecular beam epitaxy of GaN on 2H-MoS ₂ . Applied Physics Letters, 2020, 117, .	1.5	3
2	BaTiO ₃ /Al _{0.58} Ga _{0.42} N lateral heterojunction diodes with breakdown field exceeding 8 MV/cm. Applied Physics Letters, 2020, 116, .	1.5	17
3	Room Temperature Intrinsic Ferromagnetism in Epitaxial Manganese Selenide Films in the Monolayer Limit. Nano Letters, 2018, 18, 3125-3131.	4.5	567
4	Molecular beam epitaxy of 2D-layered gallium selenide on GaN substrates. Journal of Applied Physics, 2017, 121, .	1.1	52
5	Atomic Scale Structure and Defects in 2D GaSe Films and Van der Waals Interface. Microscopy and Microanalysis, 2017, 23, 1728-1729.	0.2	0
6	Large-area SnSe ₂ /GaN heterojunction diodes grown by molecular beam epitaxy. Applied Physics Letters, 2017, 111, .	1.5	11
7	High current density 2D/3D MoS ₂ /GaN Esaki tunnel diodes. Applied Physics Letters, 2016, 109, .	1.5	65
8	Exploring Thermal Properties of MoS ₂ Using In Situ Quantitative STEM. Microscopy and Microanalysis, 2016, 22, 912-913.	0.2	0
9	Layer-transferred MoS ₂ /GaN PN diodes. Applied Physics Letters, 2015, 107, .	1.5	69
10	Transferred large area single crystal MoS ₂ field effect transistors. Applied Physics Letters, 2015, 107, .	1.5	21
11	Growth and electrical characterization of two-dimensional layered MoS ₂ /SiC heterojunctions. Applied Physics Letters, 2014, 105, .	1.5	42
12	Epitaxial growth of large area single-crystalline few-layer MoS ₂ with high space charge mobility of 192 cm ² V ⁻¹ s ⁻¹ . Applied Physics Letters, 2014, 105, .	1.5	57
13	p-type doping of MoS ₂ thin films using Nb. Applied Physics Letters, 2014, 104, 092104.	1.5	268